

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-100V	45mΩ@-10V	-40A
	58mΩ@-4.5V	

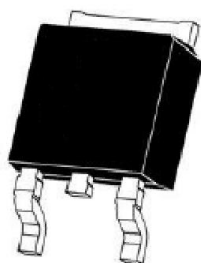
Feature

- Advanced trench technology
- Excellent $R_{DS(on)}$
- Low gate charge

Application

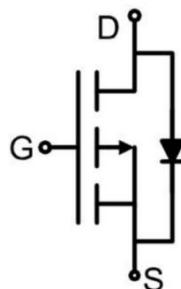
- Brushless motor
- Load switch
- Uninterruptible power supply

Package

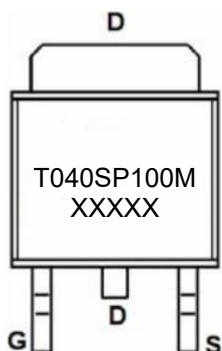


TO-252AB

Circuit diagram



Marking



Absolute maximum ratings (T_c=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	-100	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current ¹⁾ (V _{GS} =-10V)	I _D	-40	A
Continuous Drain Current ¹⁾ (V _{GS} =-10V, T _c =100°C)	I _D (100°C)	-29	A
Pulsed Drain Current ²⁾	I _{DM}	-120	A
Power Dissipation ³⁾	P _D	104	W
Single Pulse Avalanche Energy ⁴⁾	E _{AS}	560	mJ
Thermal Resistance from Junction to Case ¹⁾	R _{θJC}	1.22	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

Electrical characteristics (T_J=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250μA	-100			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =-100V, V _{GS} =0V			-1	μA
Gate-body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1.2	-1.8	-2.5	V
Drain-source on-resistance ²⁾	R _{DS(on)}	V _{GS} =-10V, I _D =-10A		38	45	mΩ
		V _{GS} =-4.5V, I _D =-8A		48	58	
Dynamic characteristics ⁶⁾						
Input Capacitance	C _{iss}	V _{DS} =-25V, V _{GS} =0V, f =1MHz		6516		pF
Output Capacitance	C _{oss}			223		
Reverse Transfer Capacitance	C _{rss}			125		
Total Gate Charge	Q _g	V _{DS} =-80V, V _{GS} =-10V I _D =-14A		92		nC
Gate-Source Charge	Q _{gs}			17.5		
Gate-Drain Charge	Q _{gd}			14		
Turn-on delay time	t _{d(on)}	V _{DS} =-50V, V _{GS} =-10V I _D =-14A, R _G =3.3Ω		20.5		nS
Turn-on rise time	t _r			32.2		
Turn-off delay time	t _{d(off)}			123		
Turn-off fall time	t _f			63.7		
Source-Drain Diode characteristics						
Diode Forward Current ^{1,5)}	I _S	V _D =V _G =0V , Force Current			-40	A
Diode Forward voltage ²⁾	V _{SD}	V _{GS} =0V, I _S =-1A			-1.2	V
Reverse Recovery Time	t _{rr}	I _F =-14A, di/dt=-100A/μs		31.2		nS
Reverse Recovery Charge	Q _{rr}			31.97		nC

Notes:

- 1) The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2) The data tested by pulsed, pulse width ≤ 300μs, duty cycle ≤ 2%.
- 3) The power dissipation is limited by 150°C junction temperature.
- 4) The EAS data shows Max. rating. The test condition is V_{DS}=-25V, V_{GS}=-10V, L=0.1mH, I_{AS}=-29A.
- 5) The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.
- 6) Guaranteed by design, not subject to production testing.

Typical Characteristics

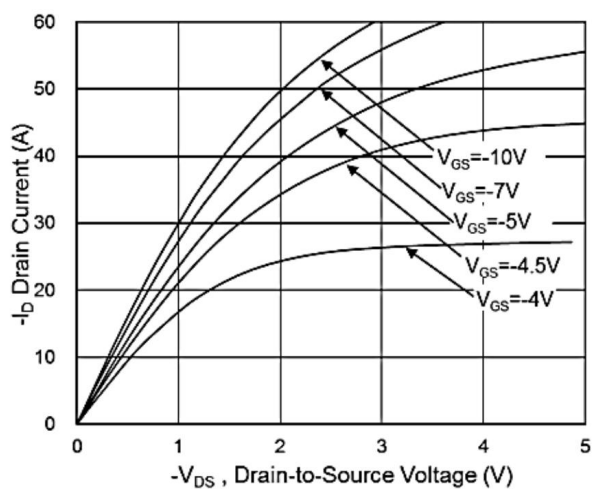


Fig.1 Typical Output Characteristics

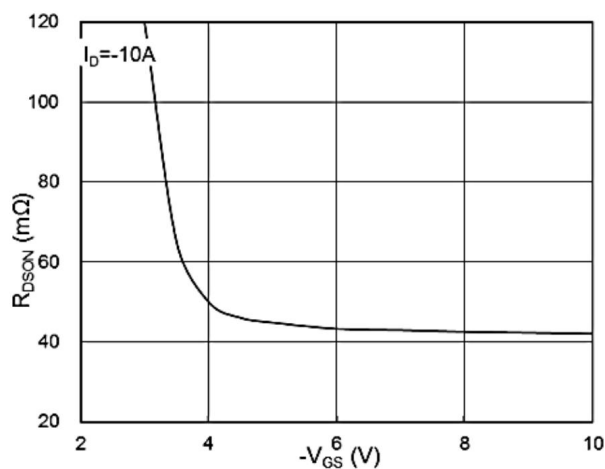


Fig.2 On-Resistance vs G-S Voltage

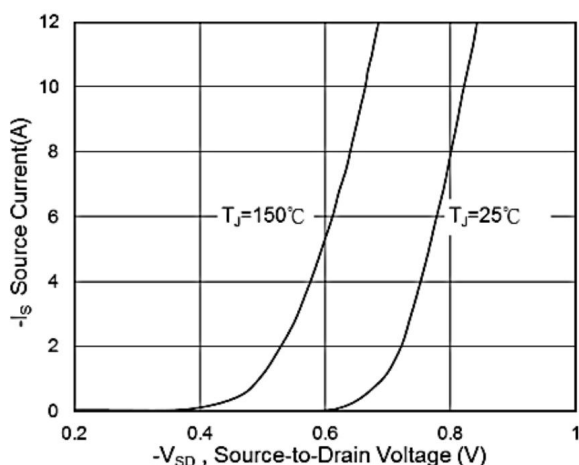


Fig.3 Typical S-D Diode Forward Voltage

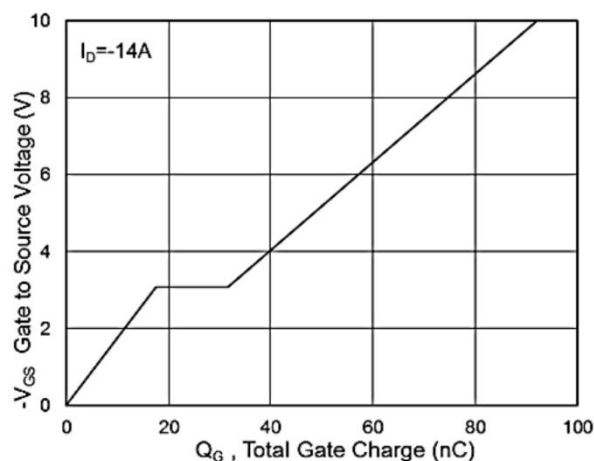


Fig.4 Gate-Charge Characteristics

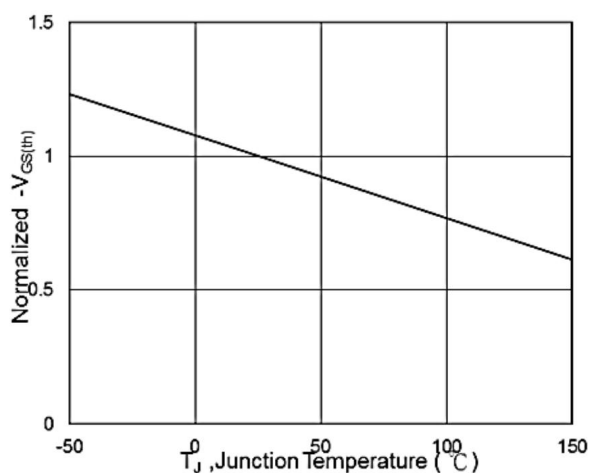


Fig.5 Normalized $V_{GS(th)}$ vs T_J

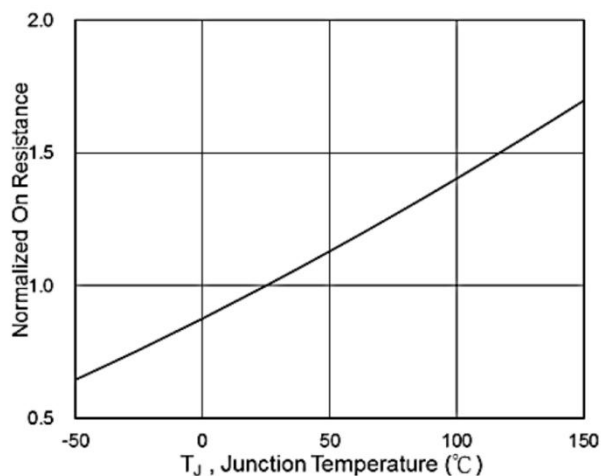


Fig.6 Normalized $R_{DS(on)}$ vs T_J

Typical Characteristics

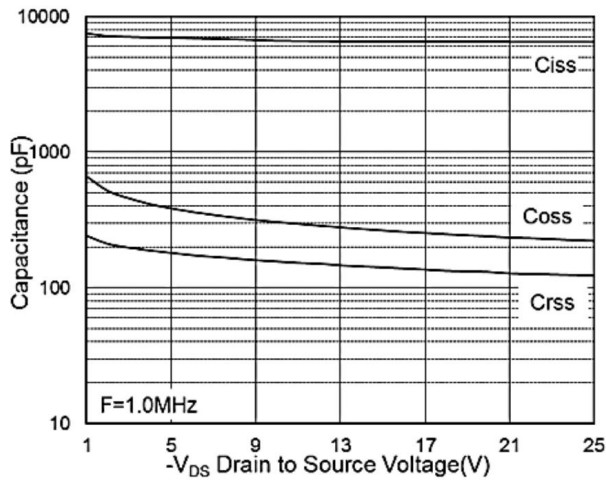


Fig.7 Capacitance

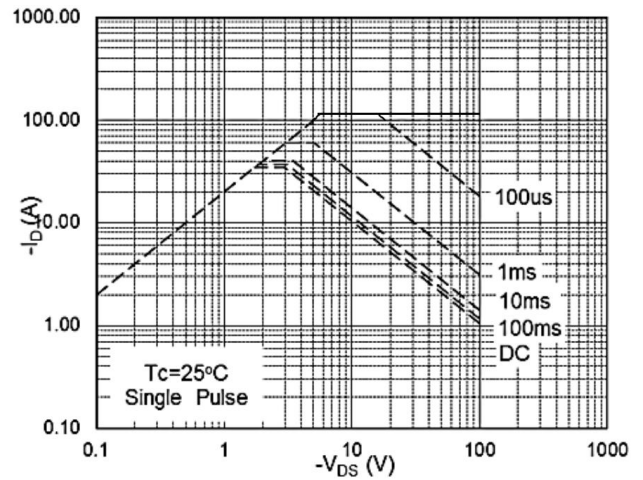


Fig.8 Safe Operating Area

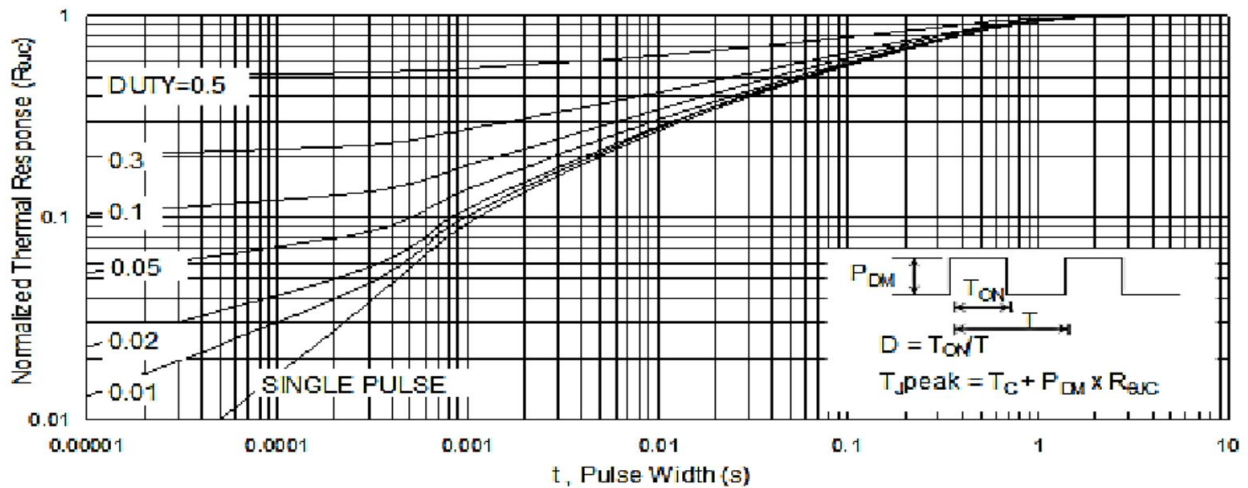


Fig.9 Normalized Maximum Transient Thermal Impedance

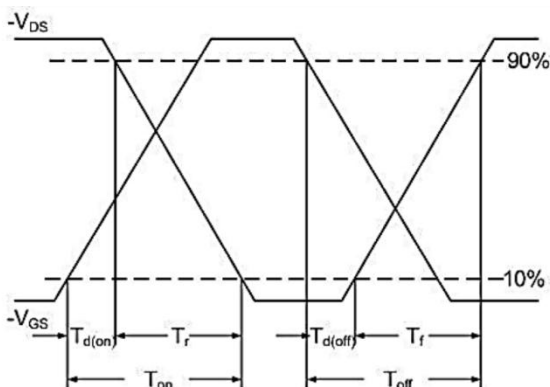


Fig.10 Switching Time Waveform

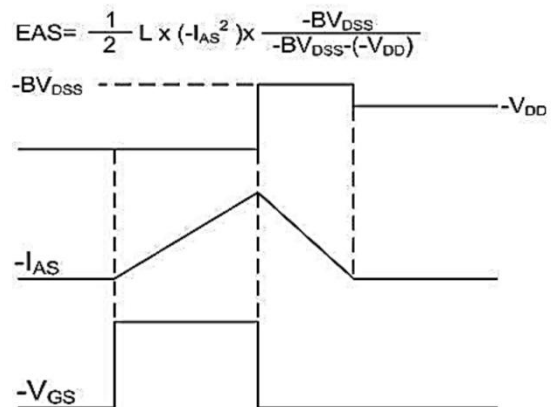
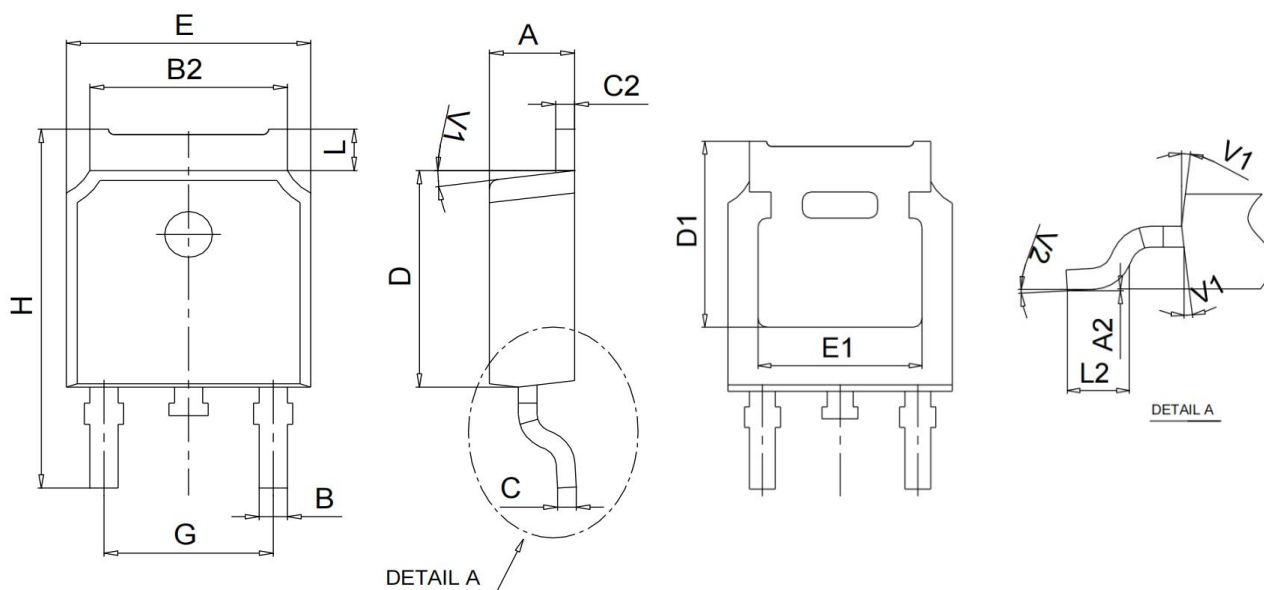


Fig.11 Unclamped Inductive Waveform

TO-252AB Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.100	2.500	0.083	0.098
A2	0.000	0.100	0.000	0.004
B	0.660	0.860	0.026	0.034
B2	5.180	5.480	0.202	0.216
C	0.400	0.600	0.016	0.024
C2	0.440	0.580	0.017	0.023
D	5.900	6.300	0.232	0.248
D1	5.300 REF.		0.209 REF.	
E	6.400	6.800	0.252	0.268
E1	4.630	-	0.182	-
G	4.470	4.670	0.176	0.184
H	9.500	10.700	0.374	0.421
L	1.090	1.210	0.043	0.048
L2	1.350	1.650	0.053	0.065
V1	7° BSC.		7° BSC.	
V2	0°	6°	0°	8°